

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
248354US-2S DIVSERIAL NO.
New Divisional Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT
Ichiro OMURA et al.FILING DATE
HerewithGROUP
Not Yet Assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	4,754,310	Jun 1988	COE			
	AB	5,637,898	Jun 1997	BALIGA			
	AC	5,998,833	Dec 1999	BALIGA			
	AD	5,801,417	Sept 1998	TSANG et al.			
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	2000-349288	12/15/00	JAPAN		
	AP	3-109775	05-1991	JAPAN		X
	AQ					X
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

FA	AW	Merchant, S., "Dependence of Breakdown Voltage on Drift Length and Buried Oxide Thickness of SOI RESURF LDMOS Transistors," Institute of Electrical and Electronics Engineers, 1993, pgs. 124-128.	<input type="checkbox"/> Additional References sheet(s) attached
	AX		
	AY		
	AZ		
Examiner	<i>[Signature]</i>		Date Considered 2/17/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.